

## CIR-W3DUSOSM1304G

DDR3 WIDE TEMP. DIMM 1333MHz 4GB

### Description

The CIR-W3DUSOSM1304G is 512M words X 64 bits, 2 ranks. Unbuffered Dual In-Line Memory Module (DIMM). DDR3 SDRAMs in Fine Ball Grid Array (FBGA) packages on a 240pin glass-epoxy substrate. Provide a high performance 8 byte interface in 133.35mm width form factor of industry standard. It is suitable for easy interchange and addition.

### Specifications

Density	4GB
Pin Count	240pin
Type	Unbuffered
Dimensions	133.35mm x 30.0mm
ECC	Non-ECC
Component Config	256M x 8 bit
Data Rate	1333 MHz
CAS Latency	9
Voltage	1.35V / 1.5V
PCB Layers	6
Operating Temp.(TCASE)	-40°C~+85°C
Module Ranks	Dual Rank

### Features

- Data rate: 1333MHz
- RoHS compliant products.
- 240pin, dual in-line memory module(DIMM)
- VDDQ= 1.35V (1.28V~1.45V) & VDDQ=1.5V(1.425V~1.575V)
- Interface: SSTL\_15
- Programmable CAS Latency(CL): 6,7,8,9 support
- Fully differential clock inputs (CK, /CK) operation
- Differential Data Strobe (DQS, /DQS)
- 8 independent internal bank
- 8K refresh cycles /64ms
- On Die Termination supported
- Asynchronous RESET pin supported
- ZQ calibration supported
- POSTED CAS additive latency (AL)
- Bi-directional Differential Data Strobe
- Burst Length: 4, 8
- 8 bit pre-fetch
- Support Industrial Temp ( -40 ~85°C )
- -tREFI 7.8us at -40 °C ≤ TCASE ≤ 85°C

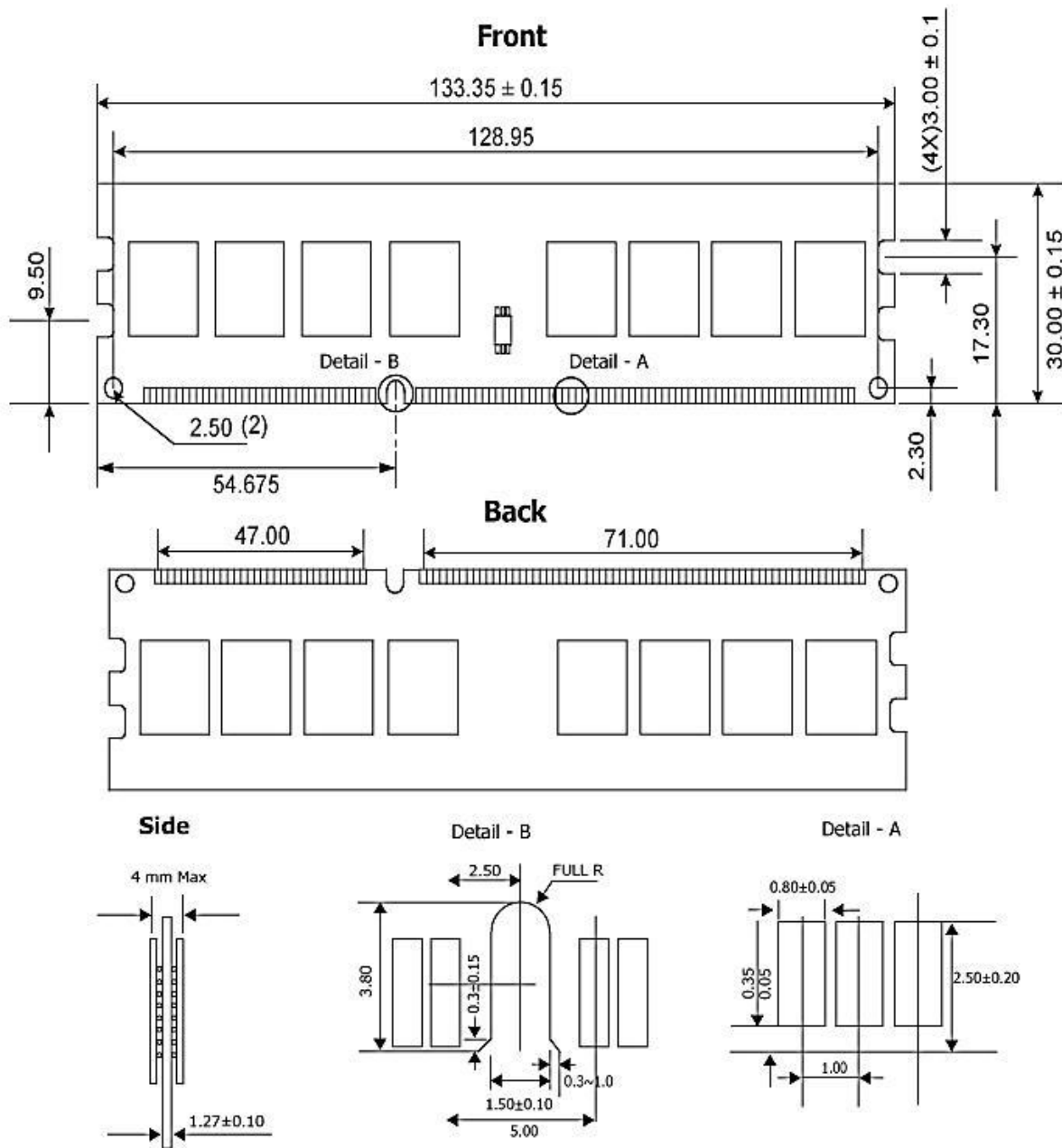


Speed Grade

Frequency Grade	Data Transfer Rate	CAS Latency Support				CL-tRCD-tRP
		CL6	CL7	CL8	CL9	
DDR3-1333	PC3-10600	800	1066	1066	1333	9-9-9

Package Dimensions

Unit: mm



Tolerances :  $\pm 0.15$ mm unless otherwise specified